

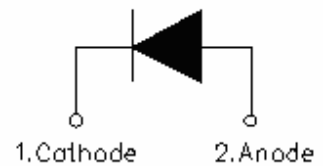
SBR1060 SCHOTTKY RECTIFIER

Applications:

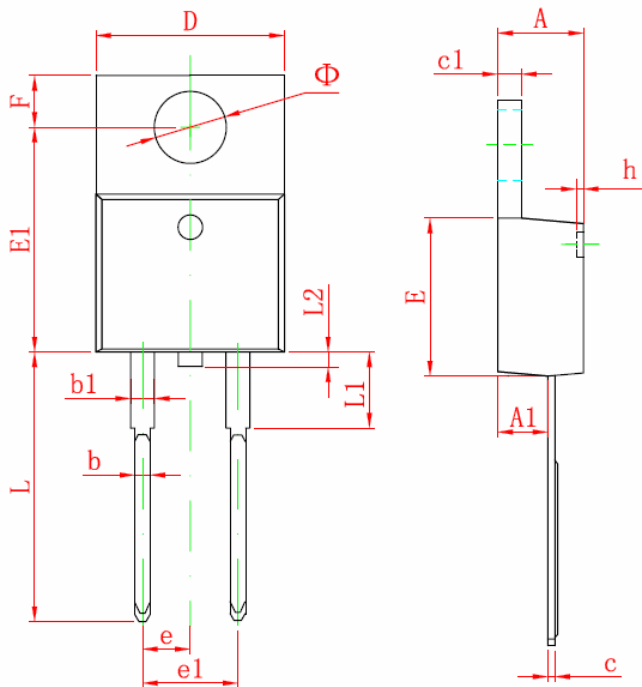
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



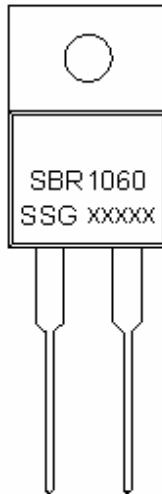
Mechanical Dimensions: In mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.470	4.670
A1	2.520	2.820
b	0.710	0.910
b1	1.170	1.370
c	0.310	0.530
c1	1.170	1.370
D	10.010	10.310
E	8.500	8.900
E1	12.060	12.460
e	2.540 TYP	
e1	4.980	5.180
F	2.590	2.890
h	0.000	0.300
L	13.400	13.800
L1	3.560	3.960
L2		1.000
Φ	3.735	3.935

TO-220AC

Marking Diagram:



Where XXXXX is YYWWL

SBR = Device Type
10 = Forward Current (10A)
60 = Reverse Voltage (60V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SBR1060	TO-220AC (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 135^\circ\text{C}$, rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	130	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	V_{F1}	@ 10A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.80	V
	V_{F2}	@ 10A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.70	V
Max. Reverse Current *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	30	mA
Max. Junction Capacitance	C_T	@ $V_R = 4\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	300	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	5.0	$^\circ\text{C/W}$
Typical Thermal Resistance, Case to Heat Sink	$R_{\theta CS}$	Mouting surface, smooth and greased	0.50	$^\circ\text{C/W}$
Approximate Weight	wt	-	1.6	g
Case Style	TO-220AC			

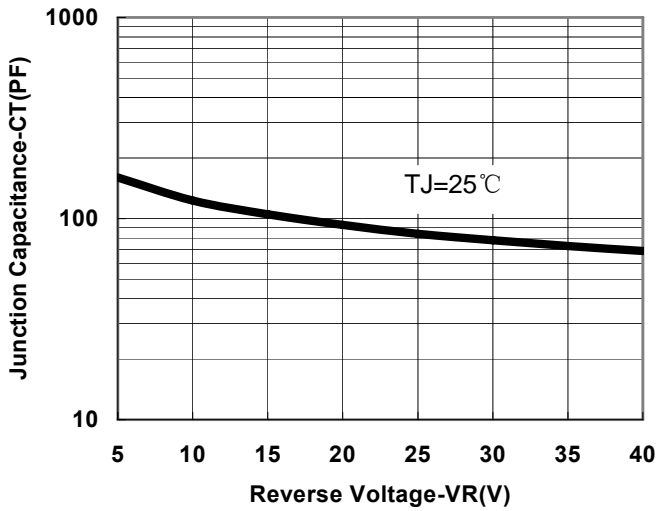


Fig.1-Typical Junction Capacitance

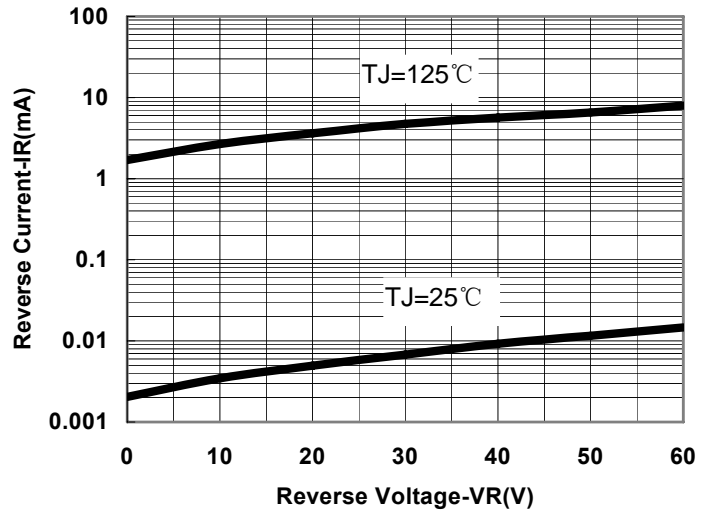


Fig.2-Typical Reverse Characteristics

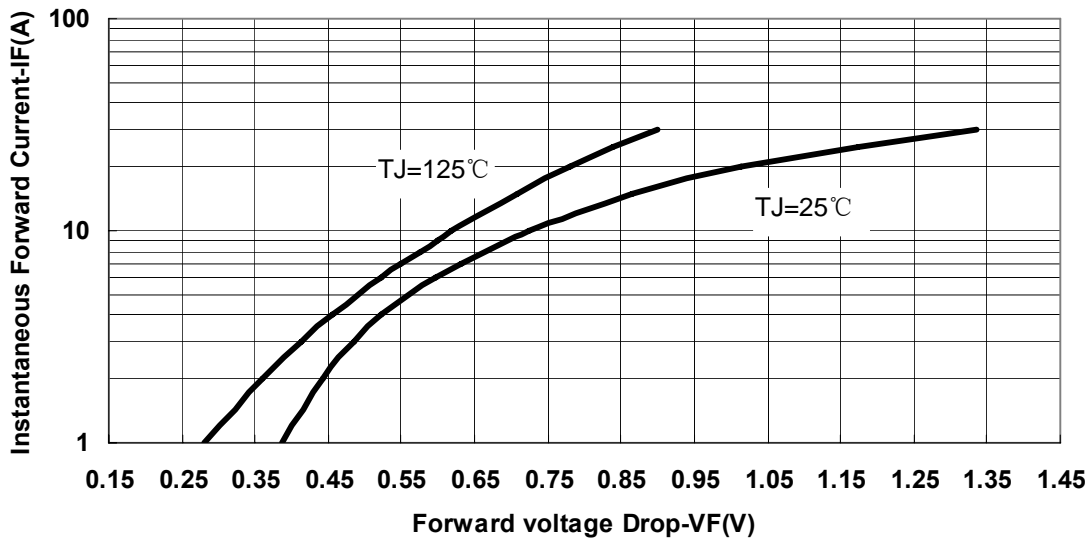


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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